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> Appl. No. 10/710,505 Amdt, dated October 4, 2005 Reply to Office action of August 08, 2005

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## REMARKS/ARGUMENTS

Reconsideration of this application is respectfully requested. Claims 1-3, 5-9 and 12-13 remain active in this case. Claims 4 and 11 have been canceled. Claims 1 and 8 have been amended in order to more particularly point out and distinctly claim that which the applicant regards as his invention. No new matter is introduced by this amendment.

Claims 1 and 8 were rejected under 35 U.S.C. 102(b), for reasons of record that can be found on pages 2-4 in the Office action identified above, which is Part of Paper No./Mail Date 20050805.

Applicant believes that Wu (US 6,586,303B2) fails to anticipate the limitations of: forming an organic non-poly spacer on sidewall of the photoresist pattern, as required by the amended claim 1 or 8. In the Office action identified above, the Examiner alleged that Wu in col. 2, lines 1-3 teaches the step of forming an organic spacer on sidewall of the photoresist pattern. Applicant respectfully disagrees with. In col. 2, lines 1-3 of Wu (US 6,586,303B2), Wu merely mentions another method for forming a lightly doped drain 15 (LDD) by utilizing a spacer as a mask, and, please see lines 13-15 of the same column, the spacer mentioned in this column is an inorganic polysilicon spacer, and also see paragraph [0008] of this application, the polysilicon spacer is difficult to remove. The difficulty of removing the polysilcion spacer is exact the major problem what the applicant of this invention is eager to solve.

Further, Wu also fails to teach that the lightly doped drain region is implanted into the substrate prior to the ion implantation of the heavily doped region, as required by the amended claim 1 or 8. It is respectfully noted that Wu teaches a method for fabricating buried bit lines of a mask ROM in which the heavily doped region is implanted first (see FIGS. 5-6).

Accordingly, reconsideration of the amended claims 1 and 8 is politely requested. As claims 2-3 and 5-7 are dependent upon claim 1, they should be allowable if the amended claim 1 is allowed. Reconsideration of claims 2-3 and 5-7 is therefore politely

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requested. As claims 9-10 and 12-13 are dependent upon claim 8, they should be allowable if the amended claim 8 is allowed. Reconsideration of claims 9-10 and 12-13 is therefore politely requested.

Applicant respectfully requests that a timely Notice of Allowance be issued in this

5 case.

Sincerely yours,

Wenton Hars

Date: October 4, 2005

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Note: Please leave a message in my voice mail if you need to talk to me. (The time in D.C. is 12 hours behind the Taiwan time, i.e. 9 AM in D.C. = 9 PM in Taiwan.)